



7th IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

March 7 – 10, 2023 / COEX Seoul, Korea

38D. Wide Bandgap Channel Devices	
Session Date:	March 9(Thu.), 2023
Session Time:	14:45-16:10
Session Room:	Room D (#308 bc)
Session Chair:	Prof. Masaharu Kobayashi (The University of Tokyo)
	Prof. ByungChul Jang (Kyungpook National University)

[38D-1] [Invited] 14:45-15:10

Avoiding Plasma Damage: MacEtch Enabled β -Ga₂O₃ FinFETs for On-Resistance Reduction and Hysteresis Elimination

Hsien-Chih Huang¹, Zhongjie Ren², A F M Anhar Uddin Bhuiyan³, Zixuan Feng³, Xixi Luo², Alex Q. Huang², Hongping Zhao³ and Xiuling Li^{1,2}

¹University of Illinois, ²University of Texas, ³The Ohio State University

[38D-2] 15:10-15:25

Demonstration of p-Channel GaN FinFETs on Silicon Substrates with Ultrahigh Current ON/OFF Ratio of 10⁹ and Reduced Interface Trap Density

Hanghai Du, Zhihong Liu, Tao Zhang, Lu Hao, Guangjie Gao, Weichuan Xing, Jincheng Zhang and Yue Hao

Xidian University

[38D-3] 15:25-15:40

Effects of Unisolated Top Gate on Performance of Dual-Gate InGaZnO Thin-Film Transistor

Chao Zhang and Xiaodong Huang

Southeast University

[38D-4] 15:40-15:55

BEOL Compatible Extremely Scaled Bilayer ITO/IGZO Channel FET with High Mobility 106 cm²/V.s

Sonu Hooda¹, Manohar Lal^{1,2}, Chen Chun-Kuei¹, Shih-Hao Tsai¹, Evgeny Zamburg^{1,2} and Aaron Voon-Yew Thean^{1,2}

¹National University of Singapore, ²Singapore Hybrid-Integrated Next-Generation μ -Electronics Centre

[38D-5] 15:55-16:10

Effects of In/Zn Composition on the Performance of Ultra-Thin Atomic Layer Deposited In_xZn_{1-x}O Channel Thin-Film Transistors

Yan-Kui Liang¹, June-Yang Zheng¹, Jing-Wei Lin¹, Yi Miao Hua¹, Tsung-Te Chou², Chun-Chieh Lu³, Huai-Ying Huang³, Yu-Ming Lin³, Chi-Chung Kei², Edward-Yi Chang¹ and Chun-Hsiung Lin¹

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